



TSM7N90CI COG Information

Heisener.com

Part Number TSM7N90CI COG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET, SINGLE, N-CHANNEL, PLANA

Package TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









TSM7N90CI C0G Specifications

Manufacturer Part Number TSM7N90CI COG Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 49nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) 25°C FET Feature - Power Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-2203 Full Pack, Isolated Tab		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Prain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C TA (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Hoput Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	TSM7N90CI C0G
Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer	TSC America Inc.
Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 49nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Ourrent - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 49nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package TiO-220 Package / Case N-Cannel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 400V 400V 40.3W Tro-220-3 Full Pack, Isolated Tab	Package	TO-220-3 Full Pack, Isolated Tab
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 Ohm @ 3.5A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 900V 7A (Tc) 7	Series	-
Drain to Source Voltage (Vdss)900VCurrent - Continuous Drain (Id) @ 25°C7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs49nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1969pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)40.3W (Tc)Rds On (Max) @ Id, Vgs1.9 Ohm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageITO-220Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature Supplier Device Package Package / Case 7A (Tc) 10V 4V @ 250μΑ 49nC @ 10V 1969pF @ 25V 430V 1969pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs49nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1969pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)40.3W (Tc)Rds On (Max) @ Id, Vgs1.9 Ohm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageITO-220Package / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	900V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Add Add Add Add Add Add Add Add Add Ad	Current - Continuous Drain (Id) @ 25°C	7A (Tc)
Gate Charge (Qg) (Max) @ Vgs 49nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1969pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	49nC @ 10V
FET Feature - Queen Dissipation (Max) 40.3W (Tc) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	1969pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 1.9 Ohm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	40.3W (Tc)
Mounting Type Through Hole Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	1.9 Ohm @ 3.5A, 10V
Supplier Device Package ITO-220 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	ITO-220
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

TSM7N90CI C0G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM7N90CI C0G Payment Methods



















TSM7N90CI C0G Shipping Methods













If you have any question about TSM7N90CI COG, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com